

21 wherein the impurity region has the same impurity concentration as a source or drain regions of the first thin film transistor.

18 ~~25~~ (Amended) An electroluminescence display device comprising:
a substrate; and

a plurality of pixels over the substrate, each of the plurality of pixels comprising:

a first thin film transistor;

a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and

22 an electroluminescence element electrically connected to the second thin film transistor, wherein the first thin film transistor comprises at least two gate electrodes over the substrate, at least two channel regions corresponding to the gate electrode, over the gate electrode with a gate insulating film interposed therebetween, and an impurity region interposed between the channel regions,

wherein a channel width of the second thin film transistor is greater than a channel width of the first thin film transistor, and

wherein the impurity region has the same impurity concentration as a source or drain regions of the first thin film transistor.

REMARKS

At the outset the Examiner is thanked for the review and consideration of the present application. Additionally, the Examiner is thanked for indicating that claims 2-4, 6, 7, 9, 10, 25-27, 29-31, 38, 39, 41, 42, 49, 50, 52 and 53 are allowable, and that claims 8, 18, 19, 21, 22, 34, 35, 45, and 46 contain allowable subject matter. Applicants respectfully note that claim 22 is understood as being objected to, although the detailed Office Action in page 4, second paragraph, has omitted claim 22 as being objected to.

The Examiner's Action dated September 3, 2002 has been received and its contents reviewed. By this amendment, claims 17 and 25 have been amended. Accordingly, claims 1-10